

In the Claims:

1. (Currently amended) A semiconductor component having a thin-film semiconductor body (2) arranged on a carrier (4),

~~characterized in that~~ wherein

the carrier (4) contains germanium.

2. (Currently amended) The semiconductor component as claimed in claim 1,

~~characterized in that~~ wherein

the thin-film semiconductor body (2) is soldered onto the carrier (4).

3. (Currently amended) The semiconductor component as claimed in claim 1 ~~or 2~~,

~~characterized in that~~ wherein

the thin-film semiconductor body (2) is soldered onto the carrier (4) by means of a gold-containing solder.

4. (Currently amended) The semiconductor component as claimed in claim 1 ~~one of claims 1 to 3~~,

~~characterized in that~~ wherein

the thin-film semiconductor body (2) comprises a plurality of individual layers.

5. (Currently amended) The semiconductor component as claimed in claim 1 ~~one of~~  
~~claims 1 to 4,~~

~~characterized in that~~ wherein

the thin-film semiconductor body (2) or at least one of the individual layers contains a  
III-V compound semiconductor.

6. (Currently amended) The semiconductor component as claimed in claim 5,

~~characterized in that~~ wherein

the thin-film semiconductor body (2) or at least one of the individual layers contains  
 $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{P}$ ,  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq x + y \leq 1$ .

7. (Currently amended) The semiconductor component as claimed in claim 5,

~~characterized in that~~ wherein

the thin-film semiconductor (2) or at least one of the individual layers contains  
 $\text{In}_x\text{As}_y\text{Ga}_{1-x-y}\text{P}$ ,  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq x + y \leq 1$ .

8. (Currently amended) The semiconductor component as claimed in claim 5,

~~characterized in that~~ wherein

the thin-film semiconductor body (2) or at least one of the individual layers contains  $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{As}$  where  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq x + y \leq 1$  or  $\text{In}_x\text{Ga}_{1-x}\text{As}_{1-y}\text{N}_y$  where  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ .

9. (Currently amended) The semiconductor component as claimed in claim 5,  
~~characterized in that~~ wherein  
the thin-film semiconductor body (2) or at least one of the individual layers contains a  
nitride compound semiconductor, in particular  $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ ,  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq x + y \leq 1$ .

10. (Currently amended) The semiconductor component as claimed in claim 1 ~~one of~~  
~~claims 1 to 9~~,

~~characterized in that~~ wherein

the thin-film semiconductor body (2) has a radiation-emitting active region.

11. (Currently amended) The semiconductor component as claimed in claim 1 ~~one of~~  
~~claims 1 to 10~~,

~~characterized in that~~ wherein

a mirror layer, preferably a metallic mirror layer, is arranged between the thin-film  
semiconductor body (2) and the carrier (4).

12. (Currently amended) The semiconductor component as claimed in claim 11,  
~~characterized in that~~ wherein  
a dielectric layer is at least partially arranged between the thin-film semiconductor body  
(2) and the mirror layer.

13. (Currently amended) A method for producing a semiconductor component having a thin-film conductor body (2) arranged on a carrier (4), having the steps of

- a) growing the thin-film semiconductor body on a substrate,
  - b) applying the carrier (4) to a side of the thin-film semiconductor body (2) that is remote from the substrate (1), and
  - c) stripping the thin-film semiconductor body (2) from the substrate,
- ~~characterized in that~~ wherein  
the carrier (4) contains germanium.

14. (Currently amended) The method as claimed in claim 13,  
~~characterized in that~~ wherein  
the substrate is eroded, in particular ground away and/or etched away, in step c).

15. (Currently amended) The method as claimed in claim 13,  
~~characterized in that~~ wherein  
the semiconductor body is stripped from the substrate (1) by laser irradiation in step c).

16. (Currently amended) The method as claimed in claim 13 ~~one of claims 13 to 15~~,  
~~characterized in that~~ wherein  
the carrier is soldered on in step b).

17. (Currently amended) The method as claimed in claim 13 ~~one of claims 13 to 16,~~  
~~characterized in that~~ wherein

a gold layer (3, 3a, 3b) is arranged on that side of the thin-film semiconductor body (2) which faces the carrier and/or on that side of the carrier which faces the thin-film semiconductor body (2), ~~which~~ and wherein said gold layer, when the carrier is soldered on in step b), at least partially forms a melt containing gold and germanium.

18. (Currently amended) The method as claimed in claim 13 ~~one of claims 13 to 17,~~  
~~characterized in that~~ wherein

prior to step b), a layer containing gold and germanium is applied on that side of the thin-film semiconductor body (2) which faces the carrier and/or on that side of the carrier which faces the thin-film semiconductor body (2).

19. (Currently amended) The method as claimed in claim 13 ~~one of claims 13 to 18,~~  
~~characterized in that~~ for producing a semiconductor component having a thin-film body arranged on a carrier that contains germanium, as claimed in one of claims 1 to 12 is produced by said method.

20. (Currently amended) The semiconductor component as claimed in claim 1, wherein one of claims 1 to 12 or the method as claimed in one of claims 13 to 19, ~~characterized in that~~ the semiconductor component is a luminescence diode, ~~in particular a light emitting diode or a laser diode.~~

21. (New) The semiconductor component as claimed in claim 20, wherein the semiconductor component is a light emitting diode or a laser diode.

22. (New) The method as claimed in claim 13, wherein the semiconductor component is a luminescence diode.

23. (New) The method as claimed in claim 22, wherein the semiconductor component is a light-emitting diode or a laser diode.